

1SS110

Silicon Epitaxial Planar Diode for Tuner Band Switch

HITACHI

ADE-208-179B (Z)
Rev. 2

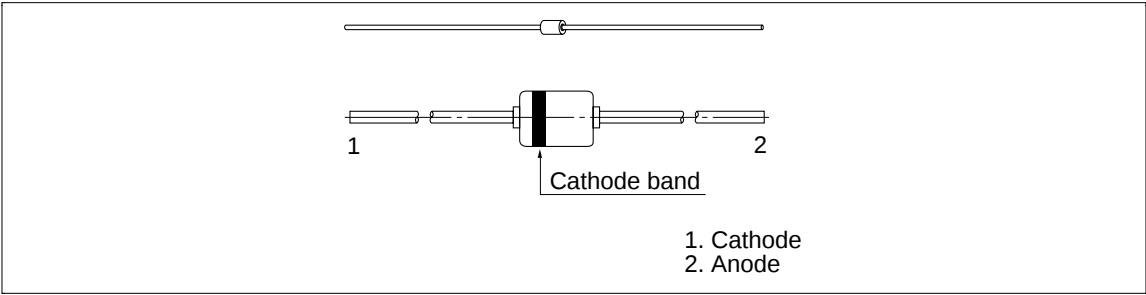
Features

- Low forward resistance. ($r_f = 0.9\Omega_{\text{max}}$)
- Suitable for 5mm pitch high speed automatical insertion.
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

Type No.	Cathode band	Package Code
1SS110	Verdure	MHD

Outline



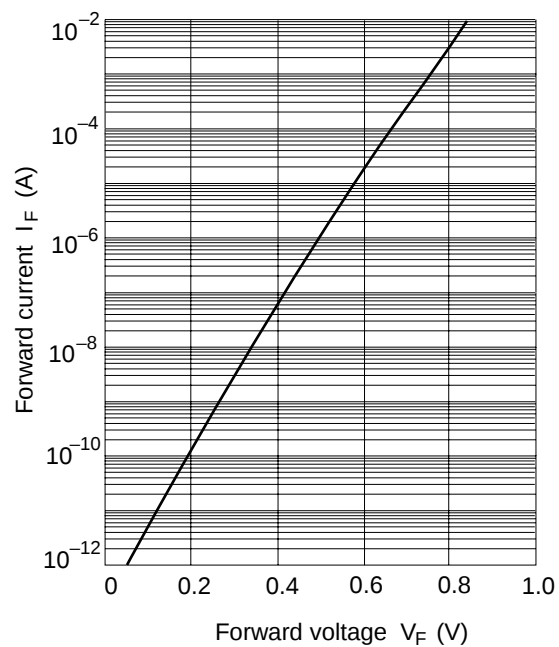
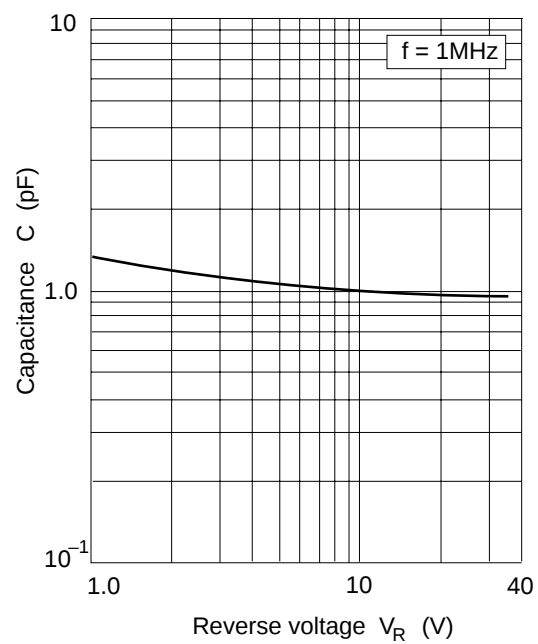
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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	35	V
Forward current	I_F	100	mA
Junction temperature	T_j	175	°C
Storage temperature	T_{stg}	−65 to +175	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	$I_F = 10\text{mA}$
Reverse voltage	V_R	35	—	—	V	$I_R = 10\mu\text{A}$
Reverse current	I_R	—	—	0.1	μA	$V_R = 25\text{V}$
Capacitance	C	—	—	1.2	pF	$V_R = 6\text{V}$, $f = 1\text{MHz}$
Forward resistance	r_f	—	—	0.9	Ω	$I_F = 2\text{mA}$, $f = 100\text{MHz}$

**Fig.1 Forward current Vs. Forward voltage****Fig.2 Capacitance Vs. Reverse voltage**

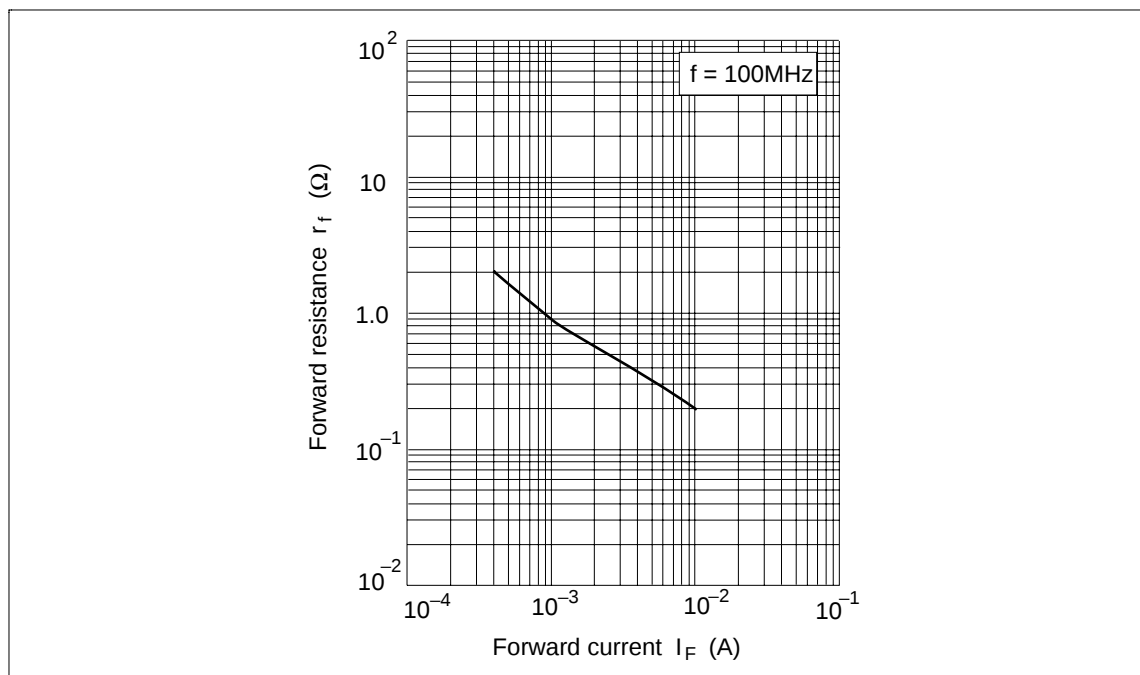


Fig.3 Forward resistance Vs. Forward current

Package Dimensions

